AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0006] of the application, which is the third full paragraph on the second pages of the application as filed with the following:

--During thermal treatments, for example to strengthen the bonding interface (which is known as "stabilizing") after detachment occurs, a gas is created in the bonding interface. In the case of a thick SOI substrate, the transferred layer is thick and fills the role of a stiffener. In the case of a thin SOI substrate in which the transferred layer and/or the oxide layer are thin, the aforementioned absorption and stiffening phenomena do not take place and [[sue]] use of a gas leads to poor bonding.--

Please replace paragraph [0027] of the application, which is the first full paragraph on the seventh pages of the application as filed with the following:

--Referring to Figure 1A, the support substrate 2 has one face 20, termed the "front face" which receives the front face 13 of the source substrate 1. Then, as represented in Figure 1B, the front face 13 of the useful layer 11 is directly bonded onto the support substrate 2 without an intermediate layer. Advantageously, this bonding is carried out via molecular adhesion. After a possible thermal annealing step, the remainder 12 is detached along the initial zone of weakness 4 by applying stresses (see Figure 1C). [[On]] One of the following techniques may be used to detach the remainder: the application of mechanical or electric stresses, chemical etching or the application of energy, for example the use of a laser, of microwaves, of an inductive heater, or a thermal treatment in an oven. These detachment techniques are known to those skilled in the art and will not be described in any further detail, and can be used alone or combined. A first rank structure (rank 1) 5 is thus obtained which includes the useful layer 11 transferred to a support substrate 2.--